

25. (New) A method of manufacturing a memory module comprising the steps of:

providing a plurality of first semiconductor devices each having protruded terminals as external terminals, and wiring portions for expanding the pitch of the protruded terminals to be wider than the pitch of the bonding electrodes of semiconductor chips in the first semiconductor devices;

providing a second semiconductor device having outer leads which are external terminals electrically connected to bonding electrodes of a semiconductor chip arranged in the second semiconductor device;

arranging the first semiconductor devices and the second semiconductor device on a module board; and

simultaneously soldering the first semiconductor devices and the second semiconductor device to mount them on the module board after the step of arranging the first semiconductor devices and the second semiconductor device on the module board.

26. (New) A method of manufacturing a memory module according to claim 25, wherein a number of the first semiconductor devices is larger than that of the second semiconductor device on the module board.

27. (New) A method of manufacturing a memory module according to claim 26, wherein each of the first semiconductor devices has a write enable input terminal.

28. (New) A method of manufacturing a memory module according to claim 27, wherein each of the first semiconductor devices is a DRAM device.

29. (New) A method of manufacturing a memory module according to claim 28, wherein the second semiconductor device is a nonvolatile read-only memory device.

30. (New) A method of manufacturing a memory module according to claim 28, wherein the second semiconductor device is an EEPROM device.

31. (New) A method of manufacturing a memory module comprising the steps of:

providing a plurality of first semiconductor devices of a chip size each having protruded terminals as external terminals, and rewirings which are wiring portions for expanding the pitch of the protruded terminals to be wider than the pitch of the bonding electrodes in the area of semiconductor chips in the first semiconductor devices;

providing a second semiconductor device having outer leads which are external terminals electrically connected to bonding electrodes of a semiconductor chip arranged in the second semiconductor device;

arranging the first semiconductor devices and the second semiconductor device on a module board; and

simultaneously soldering the first semiconductor devices and the second semiconductor device to mount them on the module board after the step of arranging the first semiconductor devices and the second semiconductor device on the module board.

32. (New) A method of manufacturing a memory module according to claim 31, wherein a number of the first semiconductor devices is larger than that of the second semiconductor device on the module board.

33. (New) A method of manufacturing a memory module according to claim 32, wherein each of the first semiconductor devices has a write enable input terminal.

34. (New) A method of manufacturing a memory module according to claim 33, wherein each of the first semiconductor devices is a DRAM device.

35. (New) A method of manufacturing a memory module according to claim 34, wherein the second semiconductor device is a nonvolatile read-only memory device.

36. (New) A method of manufacturing a memory module according to claim 34, wherein the second semiconductor device is an EEPROM device.

37. (New) A method of manufacturing a memory module comprising steps of:

providing a plurality of first semiconductor devices of a chip size having protruded terminals as external terminals arranged in the area of semiconductor chips in the first semiconductor devices;

providing a second semiconductor device having outer leads which are external terminals electrically connected to bonding electrodes of semiconductor chips arranged in the second semiconductor device;

arranging the first semiconductor devices and the second semiconductor device on a module board; and

simultaneously soldering the first semiconductor devices and the second semiconductor device to mount them on the module board after the step of arranging the first semiconductor devices and the second semiconductor device on the module board.

38. (New) A method of manufacturing a memory module according to claim 37, wherein a number of the first semiconductor devices is larger than that of the second semiconductor device on the module board.

39. (New) A method of manufacturing a memory module according to claim 38, wherein each of the first semiconductor devices has a write enable input terminal.

40. (New) A method of manufacturing a memory module according to claim 39, wherein each of the first semiconductor devices is a DRAM device.

41. (New) A method of manufacturing a memory module according to claim 40, wherein the second semiconductor device is a nonvolatile read-only memory device.

42. (New) A method of manufacturing a memory module according to claim 40, wherein the second semiconductor device is an EEPROM device.

43. (New) A method of manufacturing a memory module comprising steps of:

providing a plurality of first semiconductor devices of a chip size having protruded terminals as external terminals

arranged in the area of semiconductor chips in the first semiconductor devices;

providing a second semiconductor device having outer leads which are external terminals electrically connected to bonding electrodes of semiconductor chips arranged in the second semiconductor device;

providing a module board;

arranging the first semiconductor devices and the second semiconductor device on a module board; and

electrically connecting the first semiconductor devices and the second semiconductor devices with land pads of the module board by solder reflowing after the step of arranging the first semiconductor devices and the second semiconductor device on the module board.

44. (New) A method of manufacturing a memory module according to claim 43, wherein a number of the first semiconductor devices is larger than that of the second semiconductor device on the module board.

45. (New) A method of manufacturing a memory module according to claim 44, wherein each of the first semiconductor devices has a write enable input terminal.